

#### Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of <a href="http://www.nxp.com">http://www.nxp.com</a>, <a href="http://www.semiconductors.philips.com/">http://www.nxp.com</a>, <a href="http://www.nexperia.com/">http://www.nexperia.com/</a>, <a href="http://www.nexperia.com/">http://www.nexperia.com/</a>, <a href="http://www.nexperia.com/">use http://www.nexperia.com/</a>

Instead of sales.addresses@www.nxp.com or sales.addresses@www.semiconductors.philips.com, use salesaddresses@nexperia.com (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:

- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved

Should be replaced with:

- © Nexperia B.V. (year). All rights reserved.

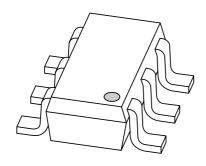
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

# DISCRETE SEMICONDUCTORS

# DATA SHEET



# **BC817DPN**NPN/PNP general purpose transistor

Product data sheet Supersedes data of 2002 Aug 09



# NPN/PNP general purpose transistor

# **BC817DPN**

#### **FEATURES**

- High current (500 mA)
- 600 mW total power dissipation
- Replaces two SOT23 packaged transistors on same PCB area.

#### **APPLICATIONS**

- · General purpose switching and amplification
- · Complementary driver
- Half and full bridge driver.

# **DESCRIPTION**

NPN/PNP transistor pair in a SOT457 (SC-74) plastic package.

#### **MARKING**

TYPE NUMBER	MARKING CODE	
BC817DPN	N4	

#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	45	V
I <sub>C</sub>	collector current (DC)	500	mA
I <sub>CM</sub>	peak collector current	1	Α

#### **PINNING**

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	

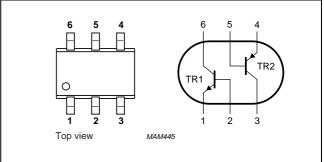


Fig.1 Simplified outline (SOT457) and symbol.

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transis	Per transistor; for the PNP transistor with negative polarity				
V <sub>CBO</sub>	collector-base voltage	open emitter	_	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	45	V
$V_{EBO}$	emitter-base voltage	open collector	_	5	V
I <sub>C</sub>	collector current (DC)		_	500	mA
I <sub>CM</sub>	peak collector current		_	1	Α
I <sub>BM</sub>	peak base current		_	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	370	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C
Per device	Per device				
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	600	mW

#### Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm<sup>2</sup>.

# NPN/PNP general purpose transistor

BC817DPN

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	208	K/W

#### Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm<sup>2</sup>.

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

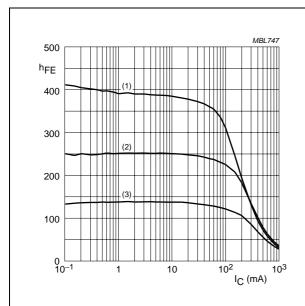
SYMBOL	PARAMETER CONDITIONS		MIN.	TYP.	MAX.	UNIT
Per transis	Per transistor unless otherwise specified; for the PNP transistor with negative polarity					
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 20 V; I <sub>E</sub> = 0	_	_	100	nA
		V <sub>CB</sub> = 20 V; I <sub>E</sub> = 0; T <sub>j</sub> = 150 °C	_	_	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0	_	_	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 1 V; I <sub>C</sub> = 100 mA; note 1	160	_	400	
		V <sub>CE</sub> = 1 V; I <sub>C</sub> = 500 mA; note 1	40	_	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 500 \text{ mA}$ ; $I_B = 50 \text{ mA}$ ; note 1	_	_	700	mV
V <sub>BE</sub>	base-emitter voltage	$V_{CE} = 1 \text{ V; } I_{C} = 500 \text{ mA;}$ notes 1 and 2	_	_	1.2	V
NPN trans	NPN transistor					
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	5	_	pF
f <sub>T</sub>	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA;}$ f = 100 MHz	100	_	_	MHz
PNP trans	PNP transistor					
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	-	9	-	pF
f <sub>T</sub>	transition frequency	$V_{CE} = -5 \text{ V; } I_{C} = -10 \text{ mA;}$ f = 100 MHz	80	_	_	MHz

# **Notes**

- 1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$
- 2.  $V_{BE}$  decreases by approximately -2 mV/K with increasing temperature.

# NPN/PNP general purpose transistor

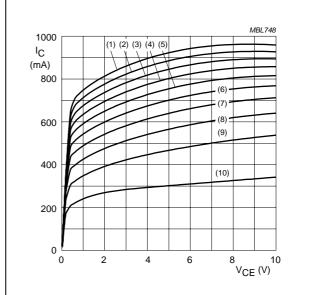
# BC817DPN



TR1 (NPN) V<sub>CE</sub> = 1 V.

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.2 DC current gain as a function of collector current; typical values.



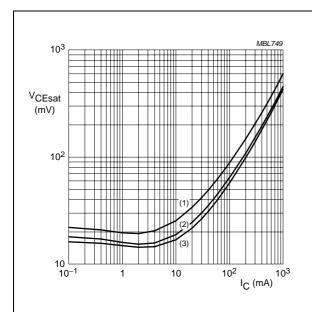
# TR1 (NPN)

- (1)  $I_B = 15 \text{ mA}.$
- (5)  $I_B = 9 \text{ mA}$ .
- (9)  $I_B = 3 \text{ mA}.$ (10)  $I_B = 1.5 \text{ mA}$ .
- (2)  $I_B = 13.5 \text{ mA}$ . (6)  $I_B = 7.5 \text{ mA}$ . (3)  $I_B = 12 \text{ mA}.$ 
  - (7)  $I_B = 6 \text{ mA}.$
- (8)  $I_B = 4.5 \text{ mA}.$ (4)  $I_B = 10.5 \text{ mA}.$

Fig.3 Collector current as a function of collector-emitter voltage; typical values.

# NPN/PNP general purpose transistor

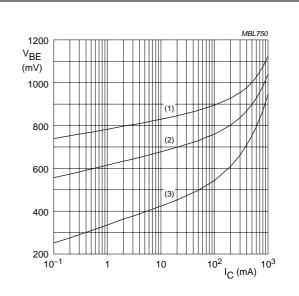
# BC817DPN



**TR1 (NPN)**  $I_{C}/I_{B} = 10$ .

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



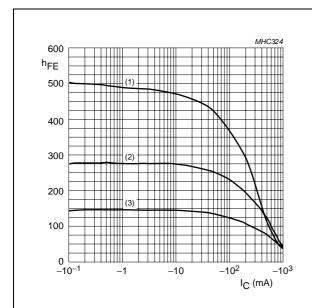
TR1 (NPN) V<sub>CE</sub> = 1 V.

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3) T<sub>amb</sub> = 150 °C.

Fig.5 Base-emitter voltage as a function of collector current; typical values.

# NPN/PNP general purpose transistor

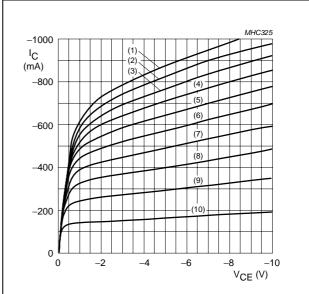
# BC817DPN



TR2 (PNP)  $V_{CE} = -1 V$ .

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.6 DC current gain as a function of collector current; typical values.



# TR2 (PNP)

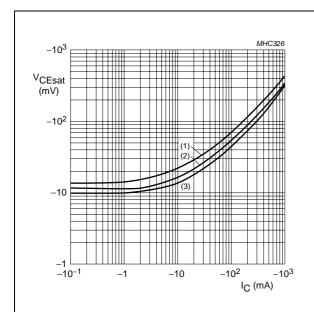
6

- (1)  $I_B = -7 \text{ mA}$ .
- (5)  $I_B = -4.2 \text{ mA}.$
- (9)  $I_B = -1.4 \text{ mA}.$ (10)  $I_B = -0.7 \text{ mA}$ .
- (2)  $I_B = -6.3 \text{ mA}.$ (3)  $I_B = -5.6 \text{ mA}.$
- (6)  $I_B = -3.5 \text{ mA}.$ (7)  $I_B = -2.8 \text{ mA}.$
- (8)  $I_B = -2.1 \text{ mA}.$ (4)  $I_B = -4.9 \text{ mA}$ .

Fig.7 Collector current as a function of collector-emitter voltage; typical values.

# NPN/PNP general purpose transistor

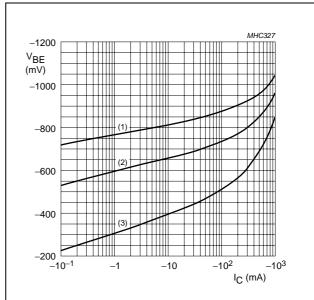
# BC817DPN



**TR2 (PNP)**  $I_{C}/I_{B} = 10$ .

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



**TR2 (PNP)**  $V_{CE} = -1 \text{ V}.$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.9 Base-emitter voltage as a function of collector current; typical values.

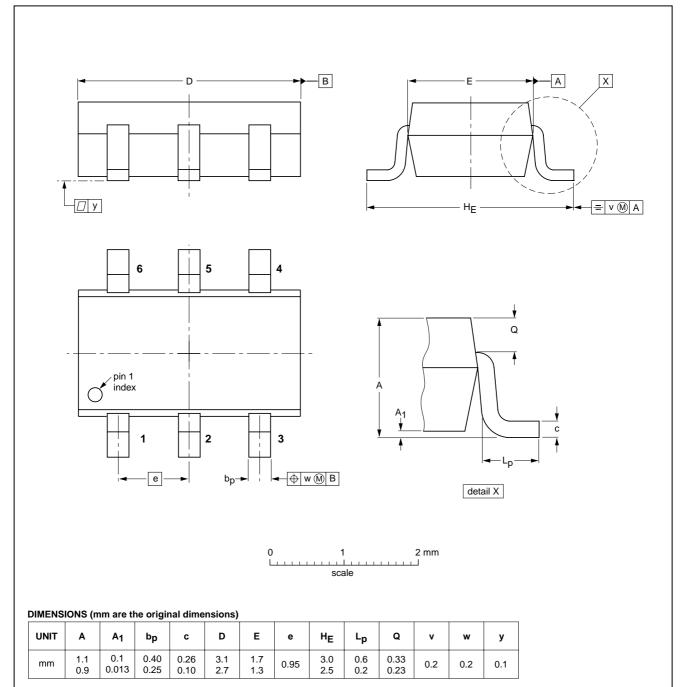
# NPN/PNP general purpose transistor

BC817DPN

# **PACKAGE OUTLINE**

Plastic surface mounted package; 6 leads

SOT457



OUTLINE	IE REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION ISSUE DATI	
SOT457			SC-74		$ \  \   \bigoplus   \big($	<del>97-02-28</del> 01-05-04

# NPN/PNP general purpose transistor

BC817DPN

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published
  and may differ in case of multiple devices. The latest product status information is available on the Internet at
  URL http://www.nxp.com.

#### **DISCLAIMERS**

**General** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

**Limiting values** — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings

System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

# **NXP Semiconductors**

# **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors. No changes were made to the content, except for the legal definitions and disclaimers.

# **Contact information**

For additional information please visit: http://www.nxp.com

For sales offices addresses send e-mail to: salesaddresses@nxp.com

© NXP B.V. 2009

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands 613514/02/pp10 Date of release: 2002 Nov 22 Document order number: 9397 750 10583

